

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	176	(yewebdar or tadesse) and ("118"/\$.ccls. or "264"/\$.ccls.)	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:07
S77	12	((("6,432,199") or ("5,705,223") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/25 16:07
S78	6	((("6,432,199") or ("5,705,223") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651")).PN. or ((2003/101929) or (2003/183250)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S84	1	("20030101929").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S85	1	("20030183250").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/25 16:12
S86	8	((("6,432,199") or ("5,705,223") or ("20030101929") or ("5,947,136") or ("5,762,709") or ("6,533,864") or ("5,940,651") or ("20030183250")).PN.	US-PGPUB; USPAT	OR	OFF	2005/02/28 09:44
S88	1	S86 and (catch\$3 and drain\$3 and trap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S89	0	S86 and de near gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S90	0	S86 and de-gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:48
S91	293	(semiconductor\$1 or wafer\$1) and de near gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:32

S92	210	(semiconductor\$1 or wafer\$1) and de-gas\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:53
S93	11	(semiconductor\$1 or wafer\$1) and (de-gas\$3 same separat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:55
S94	1364	(118/52,612).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/02/28 09:53
S95	20145	(semiconductor\$1 or wafer\$1) and (separat\$3 near5 (gas or fluid or liquid))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 09:56
S96	27	(semiconductor\$1 or wafer\$1) and (separat\$3 near5 (gas or fluid or liquid)) same liquid near trap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:31
S97	25	S96 and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 10:02
S98	27	(semiconductor\$1 or wafer\$1) and (catch near cup) same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24
S99	2	S98 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:38
S100	1	(semiconductor\$1 or wafer\$1) and (catch near cup) same frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:05

S10 1	1	(semiconductor\$1 or wafer\$1) and (catch near cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:06
S10 2	1253	(semiconductor\$1 or wafer\$1) and (cup) same (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 3	533	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 4	348	(semiconductor\$1 or wafer\$1) and (cup) near3 (frame or casing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:07
S10 5	293	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 7	15	(semiconductor\$1 or wafer\$1) and (cup) near7 (frame) and drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:08
S10 8	14	S98 and lip	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:49
S10 9	0	S86 and solvent near bath	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:24

S110	30	(semiconductor\$1 or wafer\$1) and (solvent near bath) same drain\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:56
S111	5	S110 and frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:39
S112	22	S110 and (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 11:55
S113	5	(semiconductor\$1 or wafer\$1) and (solvent near bath) same drain\$1 same (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:00
S114	31	(semiconductor\$1 or wafer\$1) and (solvent near bath) same (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:02
S115	11	(semiconductor\$1 or wafer\$1) and (solvent near bath) near5 (evaporat\$3 or saturat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 12:00
S116	1037	(430/327).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/02 16:50
S117	51	nguyen-andrew\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 16:50